

## PATENT ABSTRACTS OF JAPAN

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(11)Publication number : 2002-117697  
 (43)Date of publication of application : 19.04.2002

(51)Int.Cl. G11C 29/00  
 G01R 31/28  
 G06F 12/16  
 H01L 27/04  
 H01L 21/822

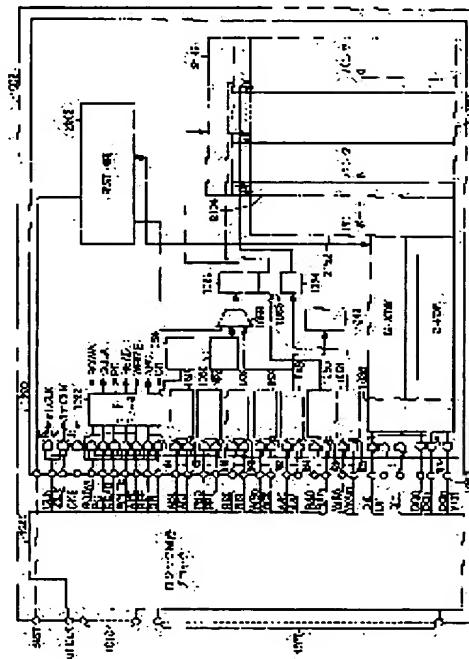
(21)Application number : 2000-307339 (71)Applicant : MITSUBISHI ELECTRIC CORP  
 (22)Date of filing : 06.10.2000 (72)Inventor : OISHI TSUKASA  
 HIDAKA HIDETO

## (54) SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE

## (57)Abstract:

**PROBLEM TO BE SOLVED:** To provide a semiconductor integrated circuit device, provided with a built-in test circuit, with which a defective memory cell can be replaced by a redundant memory cell.

**SOLUTION:** After data has been written in a memory cell array according to an internal address signal, in read-out operation, read-out data from each memory cell is compared with expected value data. A row decoder 2142 selects plural memory cells, belonging to the same row of the memory cell array en bloc according to the address signal. A BIST circuit 2002 discriminates carrying out of relieving in a spare memory cell row, rather than in a spare memory cell column, when plural defective memory cells are detected in plural memory cells selected en bloc.



## LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

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[Date of requesting appeal against examiner's  
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